

Claims 55-75 (renumbered) have been cancelled without prejudice, and are pending in the corresponding divisional application (filed March 7, 2002).

Claims 1, 12, 31 and 32 have been amended. Claims 2-11, 15-19, 22-25, 36-37 and 38-75 (renumbered 55-75) have been cancelled. Claims 76-141 have been added. A redline version is enclosed to illustrate the amendments to the claims.

### **IN THE SPECIFICATION**

Please amend the specification, as follows:

At page 9, lines 13-18, revise the text as follows:

According to the method, the cleaning composition is applied to the wafer 30 for removal of at least a portion of the low-k dielectric layer [36] 16 from the surface [34] 14 of the silicon-comprising substrate [32] 12. **FIG. 2B** depicts the portion of the wafer 30 after cleaning. As depicted, the thickness  $T_1$ , of the low-k dielectric layer [36] 16 has been reduced to thickness  $T_2$  by the removal process. The low-k dielectric layer [36] 16 can also be completely removed to produce a hydrophobic, oxide-free silicon surface [34] 14 as depicted in **FIG. 1B**.

At page 10, line 6 delete "for a low-k dielectric:photoresist" and insert therefor --(low-k dielectric:photoresist)--.

At page 10, line 22, delete "for a low-k dielectric:photoresist" and insert therefor --(photoresist:low-k dielectric)--.

At page 11, line 9, delete "for a low-k material relative to a polymeric photoresist material" and insert therefore --(polymeric photoresist material:low-k material)--.

### **IN THE DRAWINGS**

Please replace FIGS. 1A-3B (informal) with the enclosed formal drawings for FIGS. 1A-3B. No new matter is added.